

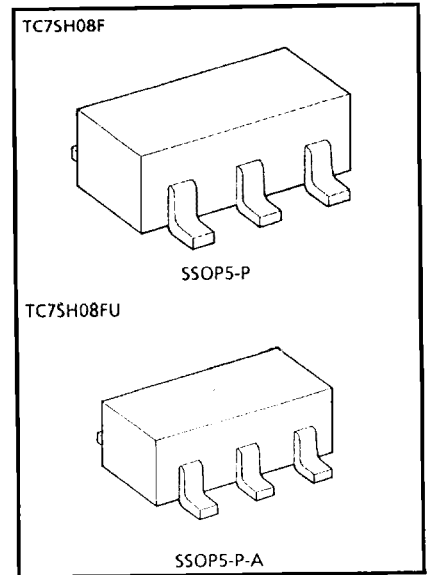
TC7SH08F, TC7SH08FU

2-INPUT AND GATE

The TC7SH08 is an advanced high speed CMOS 2-INPUT AND GATE fabricated with silicon gate C²MOS technology. It achieves the high speed operation similar to equivalent Bipolar Schottky TTL while maintaining the CMOS low power dissipation. The internal circuit is composed of 4 stages including buffer output, which provide high noise immunity and stable output. An input protection circuit ensures that 0 to 7V can be applied to the input pins without regard to the supply voltage. This device can be used to interphase 5V to 3V systems and two supply systems such as battery back up. This circuit prevents device destruction due to mismatched supply and input voltages.

FEATURES

- High Speed $t_{pd} = 4.3\text{ns}$ (Typ.) at $V_{CC} = 5\text{V}$
- Low Power Dissipation $I_{CC} = 2\mu\text{A}$ (Max.) at $T_a = 25^\circ\text{C}$
- High Noise Immunity $V_{NIH} = V_{NIL} = 28\% V_{CC}$ (Min.)
- Power Down Protection is provided on all inputs.
- Balanced Propagation Delays $t_{pLH} \approx t_{pHL}$
- Wide Operating Voltage Range $V_{CC}(\text{opr}) = 2 \sim 5.5\text{V}$

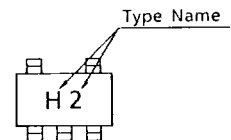


Weight SSOP5-P : 0.016g (Typ.)
 SSOP5-P-A : 0.006g (Typ.)

MAXIMUM RATINGS

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage Range	V_{CC}	-0.5~7.0	V
DC Input Voltage	V_{IN}	-0.5~7.0	V
DC Output Voltage	V_{OUT}	-0.5~ $V_{CC} + 0.5$	V
Input Diode Current	I_{IK}	-20	mA
Output Diode Current	I_{OK}	±20	mA
DC Output Current	I_{OUT}	±25	mA
DC V_{CC} / Ground Current	I_{CC}	±50	mA
Power Dissipation	P_D	200	mW
Storage Temperature	T_{stg}	-65~150	°C
Lead Temperature (10s)	T_L	260	°C

MARKING

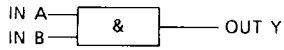


TRUTH TABLE

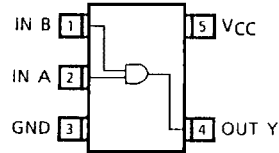
A	B	Y
L	L	L
L	H	L
H	L	L
H	H	H

TC7SH08F, TC7SH08FU

LOGIC DIAGRAM



PIN ASSIGNMENT (TOP VIEW)



RECOMMENDED OPERATING CONDITIONS

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage	V_{CC}	2.0~5.5	V
Input Voltage	V_{IN}	0~5.5	V
Output Voltage	V_{OUT}	0~ V_{CC}	V
Operating Temperature	T_{opr}	-40~85	°C
Input Rise and Fall Time	d_t/d_v	0~100 ($V_{CC} = 3.3 \pm 0.3V$)	ns/V
		0~20 ($V_{CC} = 5 \pm 0.5V$)	

DC ELECTRICAL CHARACTERISTICS

PARAMETER	SYMBOL	TEST CIRCUIT	TEST CONDITION	$T_a = 25^\circ\text{C}$			$T_a = -40 \sim 85^\circ\text{C}$		UNIT		
				V_{CC}	MIN.	TYP.	MAX.	MIN.		MAX.	
High-Level Input Voltage	V_{IH}	—	—	2.0 3.0~ 5.5	1.50 V_{CC} $\times 0.7$	— —	— —	1.50 V_{CC} $\times 0.7$	— —	V	
Low-Level Input Voltage	V_{IL}	—	—	2.0 3.0~ 5.5	— —	— —	0.50 V_{CC} $\times 0.3$	— —	0.50 V_{CC} $\times 0.3$	V	
High-Level Output-Voltage	V_{OH}	—	$V_{IN} = V_{IH}$	$I_{OH} = -50\mu\text{A}$	2.0	1.9	2.0	—	1.9	—	V
					3.0	2.9	3.0	—	2.9	—	
					4.5	4.4	4.5	—	4.4	—	
Low-Level Output-Voltage	V_{OL}	—	$V_{IN} = V_{IH}$ or V_{IL}	$I_{OL} = 50\mu\text{A}$	2.0	—	0.0	0.1	—	0.1	V
					3.0	—	0.0	0.1	—	0.1	
					4.5	—	0.0	0.1	—	0.1	
Input Leakage Current	I_{IN}	—	$V_{IN} = 5.5V$ or GND	0~ 5.5	—	—	—	± 0.1	—	± 1.0	μA
					—	—	—	—	—	—	
					—	—	—	—	—	—	
Quiescent Supply Current	I_{CC}	—	$V_{IN} = V_{CC}$ or GND	5.5	—	—	2.0	—	20.0	μA	

AC ELECTRICAL CHARACTERISTICS (Input $t_r = t_f = 3ns$)

PARAMETER	SYMBOL	TEST CIR-CUIT	TEST CONDITION		Ta = 25°C			Ta = -40~85°C		UNIT	
			V _{CC} (V)	C _L (pF)	MIN.	TYP.	MAX.	MIN.	MAX.		
Propagation Delay Time	t _{PLH}	—	—	3.3 ± 0.3	15	—	6.2	8.8	1.0	10.5	ns
					50	—	8.7	12.3	1.0	14.0	
	t _{PHL}			5.0 ± 0.5	15	—	4.3	5.9	1.0	7.0	
					50	—	5.8	7.9	1.0	9.0	
Input Capacitance	C _{IN}	—	—	—	4	10	—	10	pF		
Power Dissipation Capacitance	C _{PD}	—	Note (1)	—	14	—	—	—			

Note (1) : C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation :

$$I_{CC(opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}$$

INPUT EQUIVALENT CIRCUIT

